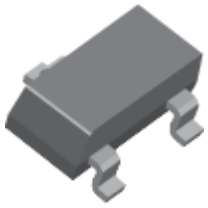
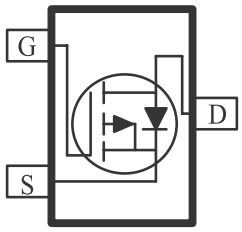
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (OHM)	I_D (A)
-20	0.100 @ V_{GS} = -4.5V	-2.9
	0.160 @ V_{GS} = -2.5V	-2.3
	0.290 @ V_{GS} = -1.8V	-1.7





ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±12	
Continuous Drain Current[a]	T_A=25°C	I_D	-2.9	A
	T_A=70°C		-2.4	
Pulsed Drain Current[b]		I_{DM}	-10	
Continuous Source Current (Diode Conduction)[a]		I_S	±1.6	A
Power Dissipation[a]	T_A=25°C	P_D	1.25	W
	T_A=70°C		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	t <= 5 sec	R_{THJA}	100	°C/W
	Steady-State		166	

Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 uA	-0.70			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = +/-12 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -16 V, V_{GS} = 0 V			-1	uA
		V_{DS} = -16 V, V_{GS} = 0 V, T_J = 55°C			-10	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -4.5 V	-3			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = -4.5 V, I_D = -2.9 A			0.100	Ω
		V_{GS} = -2.5 V, I_D = -2.3 A			0.160	
		V_{GS} = -1.8 V, I_D = -1.7 A			0.290	
Forward Tranconductance[A]	g_{fs}	V_{DS} = -5 V, I_D = -2.8 A		3		S
Diode Forward Voltage	V_{SD}	I_S = -1.6 A, V_{GS} = 0 V		-0.70		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -5 V, V_{GS} = -4.5 V, I_D = -2.6 A		6.0		nC
Gate-Source Charge	Q_{gs}			0.80		
Gate-Drain Charge	Q_{gd}			1.30		
Input Capacitance	C_{iss}	P-Channel V_{DS}=-15V, V_{GS}=0V, f=1MHz		451		pF
Output Capacitance	C_{oss}			130		
Reverse Transfer Capacitance	C_{rss}			33		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -5 V, R_L = 5 OHM, V_{GEN} = -4.5 V, R_G = 6 OHM		6.5		ns
Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(off)}$			31		
Fall-Time	t_f			21		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics

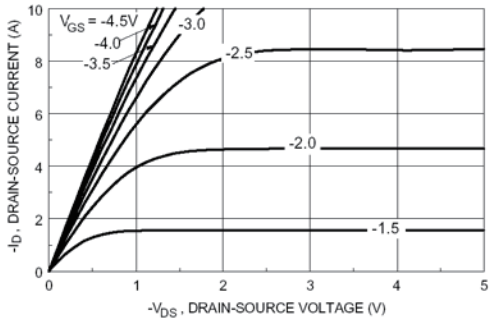


Figure 1. On-Region Characteristics.

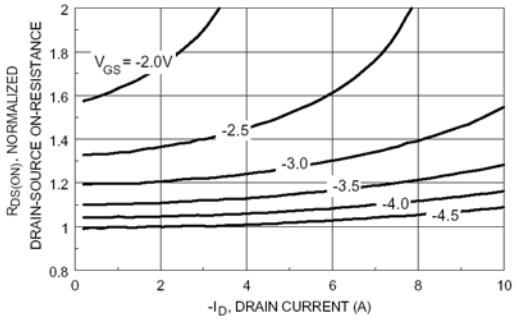


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

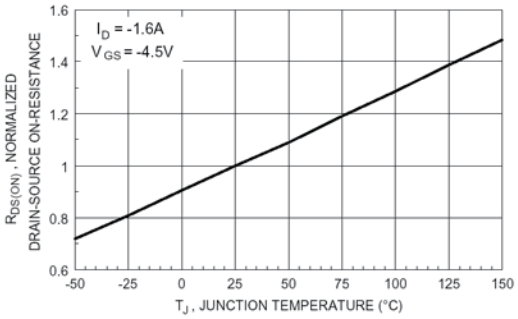


Figure 3. On-Resistance Variation with Temperature.

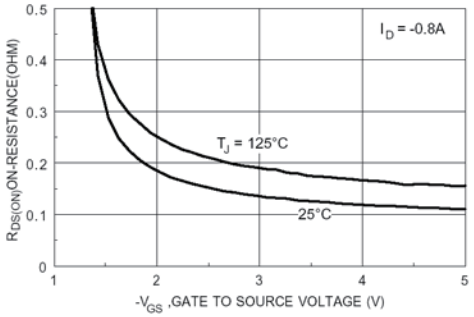


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

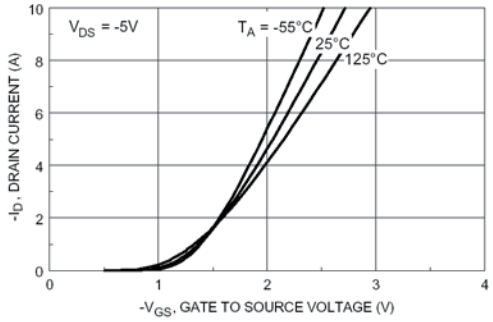


Figure 5. Transfer Characteristics.

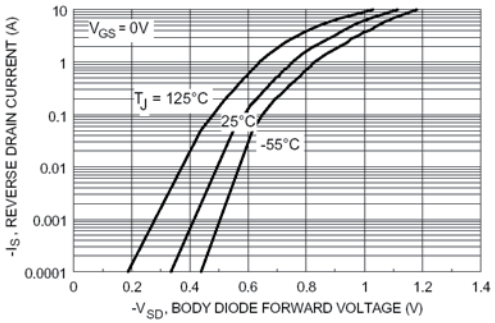


Figure 6 . Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics

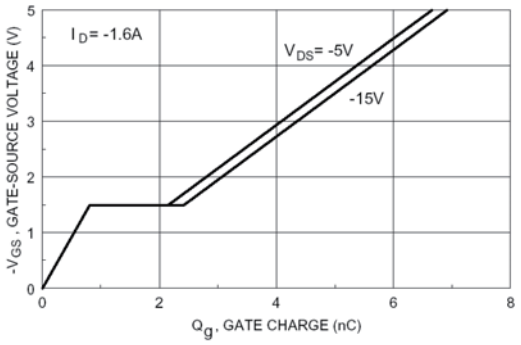


Figure 7. Gate Charge Characteristics.

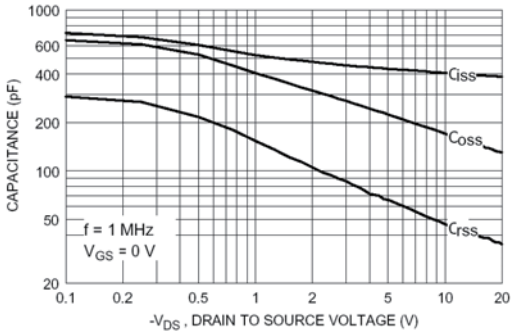


Figure 8. Capacitance Characteristics.

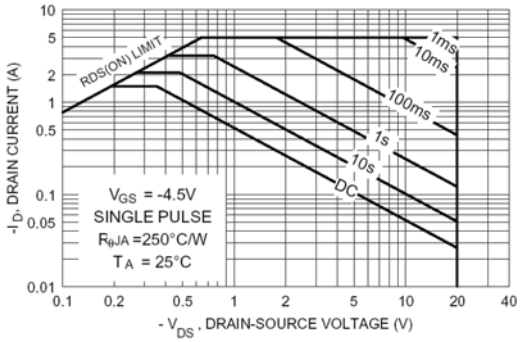


Figure 9. Maximum Safe Operating Area.

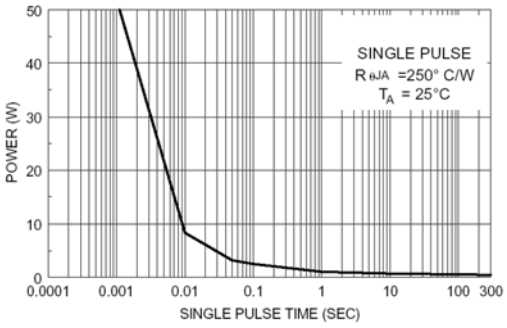


Figure 10. Single Pulse Maximum Power Dissipation.

Normalized Thermal Transient Junction to Ambient

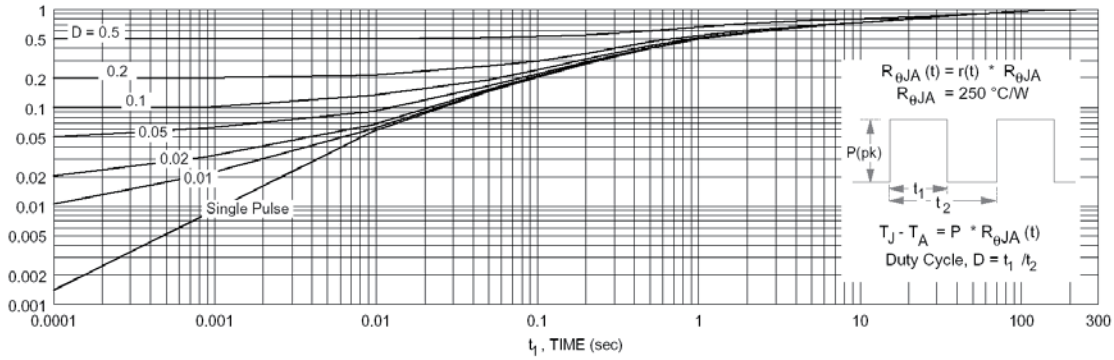
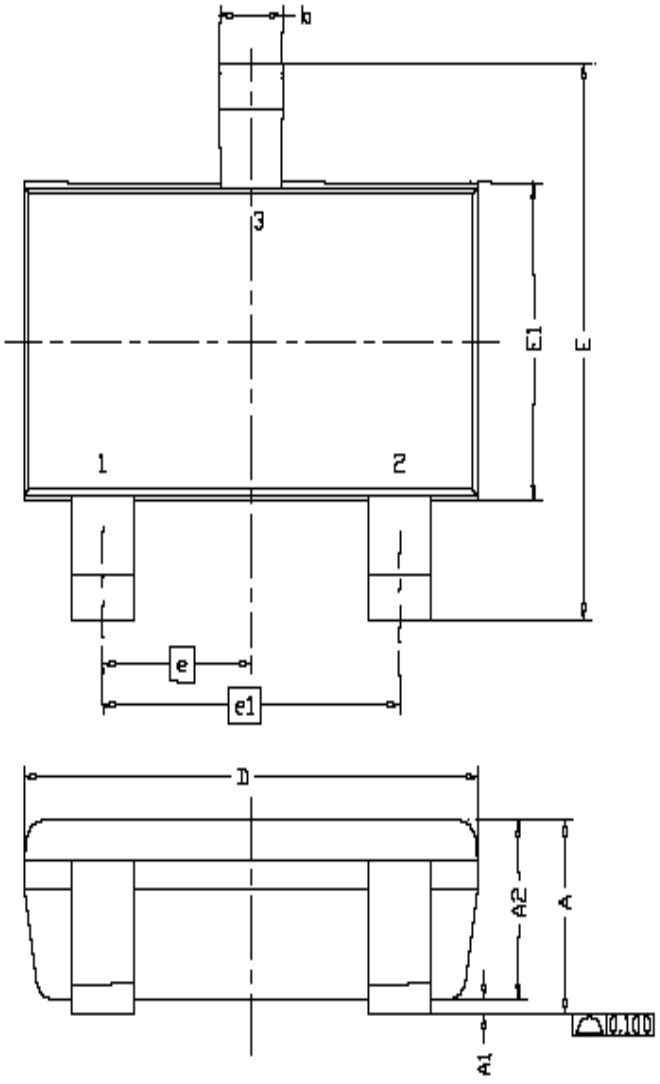
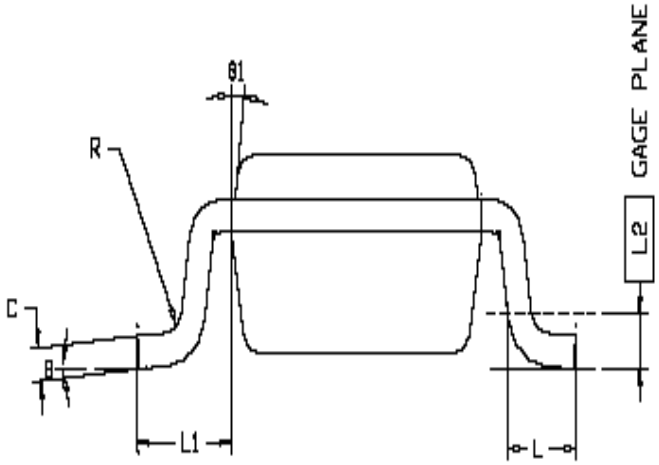


Figure 11. Transient Thermal Response Curve.

Package Information



DIM.	MILLIMETERS		
	MIN	NOM	MAX
A	0.935	0.95	1.10
A1	0.01	---	0.10
A2	0.85	0.90	0.925
b	0.30	0.40	0.50
c	0.10	0.15	0.25
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.60
L1	0.60REF		
L2	0.25BSC		
R	0.10	---	---
θ	0°	4°	8°
θ1	7°NOM		



Ordering information

- AM2323P-T1-XX
  - A: Analog Power
  - M: MOSFET
  - 2323: Part number
  - P: P-Channel
  - T1: Tape & reel
  - XX: Blank: Standard
    PF: Leadfree